

ABSTRACT OF THE DISCLOSUREPROCESS FOR MAKING A SEMICONDUCTOR DEVICE WITH SELF-ALIGNED
METALLISATIONS

This invention relates to a process for making a semiconductor device comprising the following steps:

- a doped region with a first type of conductivity is made on a first principal face of a semiconductor substrate and at least one window is made,
- a first metallisation area is deposited on the doped region,
- a dielectric layer is deposited on at least the window and the first metallisation area,
- at least a first opening is etched in the dielectric layer at the window to accommodate a doped region with a second type of conductivity while arranging an undoped portion of the semiconductor substrate laterally between the doped regions,
- the substrate is doped to create the doped region with the second type of conductivity,
- a second metallisation area is deposited.

Application particularly for solar cells in thin layer.